

## **IN THE CLAIMS**

This listing of claims will replace all prior versions and listings of claims in the application:

### **LISTING OF CLAIMS:**

1. (Currently Amended) A method for forming a contact plug in a semiconductor device, comprising the steps of:

forming a contact isolation layer on a substrate, the contact isolation layer having an opening exposing a partial portion of the substrate;

depositing a conductive layer within the opening of the contact isolation layer;

doping dopants in a manner to allow the conductive layer to have different doping distributions with respect to a thickness; and

forming a contact plug within the opening through a planarization process applied to the conductive layer,

wherein the step of doping the dopants further includes:

a first step of doping the dopants until reaching a target deposition thickness by gradually increasing a concentration of the dopants from a first concentration to a second concentration for an interval between an initial conductive layer deposition and the target deposition thickness; and

a second step of doping the dopants in a manner that the second concentration is consistently maintained throughout for an interval from the target deposition thickness to a complete deposition thickness.

2. (Cancelled)

3. (Currently Amended) The method as recited in claim 2 1, wherein, at the first step, a flow quantity of a doping gas initially added is low and is gradually increased so that the doping concentration of the dopants increases from the first concentration to the second concentration.

4. (Currently Amended) The method as recited in claim 2 1, wherein, at the second step, a high flow quantity of a doping gas is added and remained the same throughout so that the doping concentration of the dopants is consistently maintained to be the second concentration.

5. (Currently Amended) The method as recited in claim 2 1, wherein the complete deposition thickness after depositing the conductive layer ranges from about 3000 Å to about 3500 Å, and

the target deposition thickness ranges from about 500 Å to about 1000 Å.

6. (Currently Amended) The method as recited in claim 2 1, wherein the first concentration ranges from about  $5 \times 10^{18}$  dopants/cm<sup>3</sup> to about  $1 \times 10^{20}$  dopants/cm<sup>3</sup>, and the second concentration ranges from about  $1 \times 10^{20}$  dopants/cm<sup>3</sup> to about  $3 \times 10^{20}$  dopants/cm<sup>3</sup>.

7. (Currently Amended) The method as recited in claim 3, wherein the doping gas is ~~PH<sub>3</sub>~~ PH<sub>3</sub> gas.

8. (Currently Amended) The method as recited in claim 1, wherein the conductive layer is ~~either~~ selected from a group consisting of a polysilicon layer ~~or~~ and a polysilicon germanium layer.

9. (Currently Amended) A method for forming a contact plug in a semiconductor device, comprising the steps of:

forming a contact isolation layer on a substrate, the contact isolation layer having an opening exposing a partial portion of the substrate;

depositing a conductive layer within the opening of the contact isolation layer; and

forming a contact plug within the opening through a planarization process applied to the conductive layer,

wherein the step of depositing the conductive layer includes a step of doping dopants in a manner to allow the conductive layer to have different doping distributions with respect to a thickness of the conductive layer,

wherein the step of doping the dopants further includes:

a first step of doping the dopants until reaching a target deposition thickness by gradually increasing a concentration of the dopants from a first concentration to a second concentration for an interval between an initial conductive layer deposition and the target deposition thickness; and

a second step of doping the dopants in a manner that the second concentration is consistently maintained throughout for an interval from the target deposition thickness to a complete deposition thickness.

10. (Cancelled)

11. (Currently Amended) The method as recited in claim ~~10~~ 9, wherein, at the first step, a flow quantity of a doping gas

initially added is low and is gradually increased so that the doping concentration of the dopants increases from the first concentration to the second concentration.

12. (Currently Amended) The method as recited in claim ~~10~~ 9, wherein, at the second step, a high flow quantity of a doping gas is added and remained the same throughout so that the doping concentration of the dopants is consistently maintained to be the second concentration.

13. (Currently Amended) The method as recited in claim ~~10~~ 9, wherein the complete deposition thickness after depositing the conductive layer ranges from about 3000 Å to about 3500 Å, and the target deposition thickness ranges from about 500 Å to about 1000 Å.

14. (Currently Amended) The method as recited in claim ~~10~~ 9, wherein the first concentration ranges from about  $5 \times 10^{18}$  dopants/cm<sup>3</sup> to about  $1 \times 10^{20}$  dopants/cm<sup>3</sup>, and the second concentration ranges from about  $1 \times 10^{20}$  dopants/cm<sup>3</sup> to about  $3 \times 10^{20}$  dopants/cm<sup>3</sup>.

15. (Currently Amended) The method as recited in claim 11,  
wherein the doping gas is ~~PH<sub>3</sub>~~ PH<sub>3</sub> gas.

16. (Currently Amended) The method as recited in claim 9,  
wherein the conductive layer is ~~either~~ selected from a group  
consisting of a polysilicon layer ~~or~~ and a polysilicon germanium  
layer.